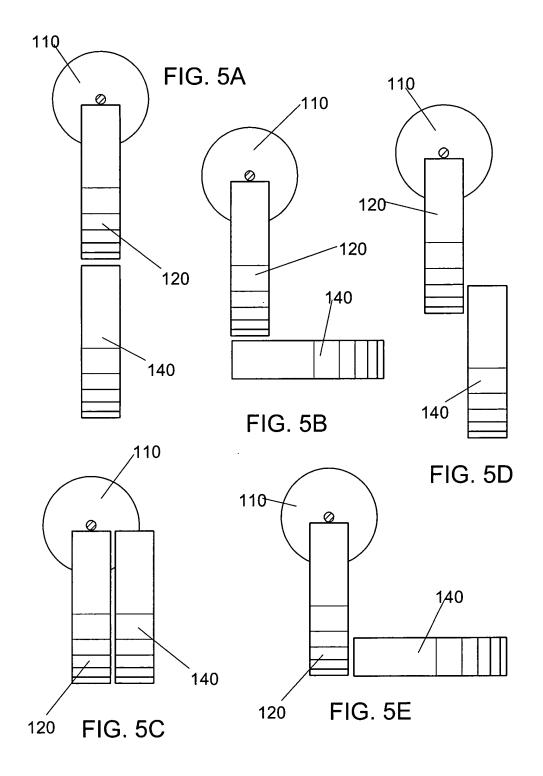
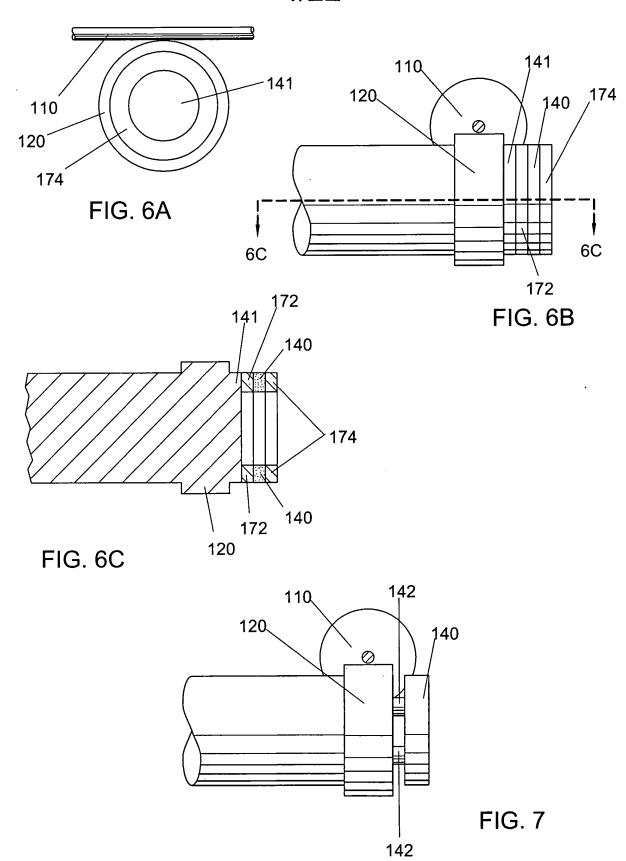


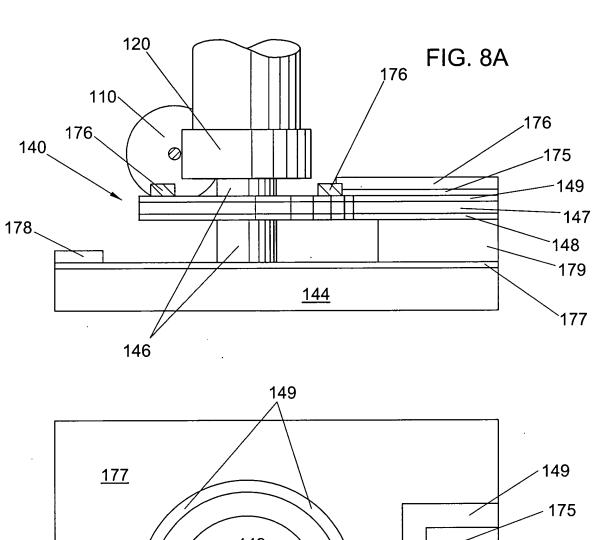
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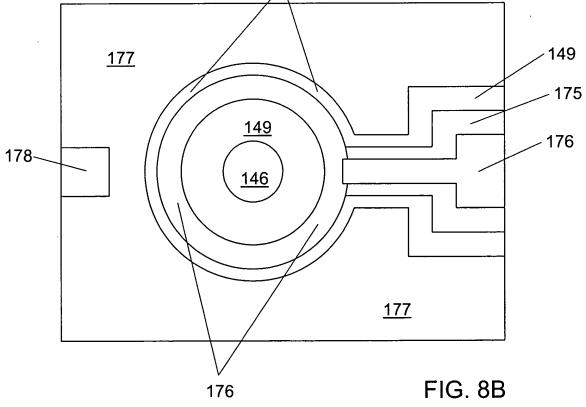


A. S. C.



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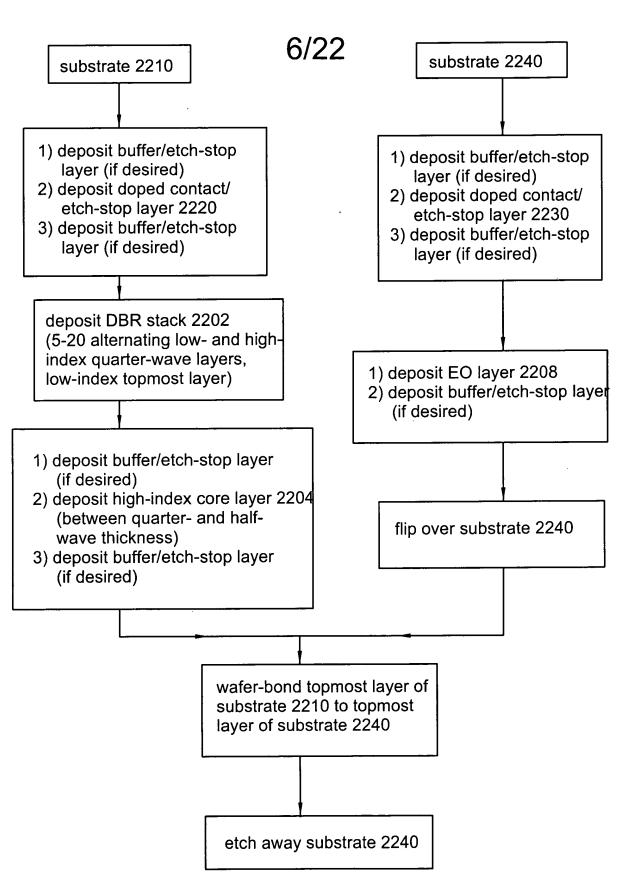
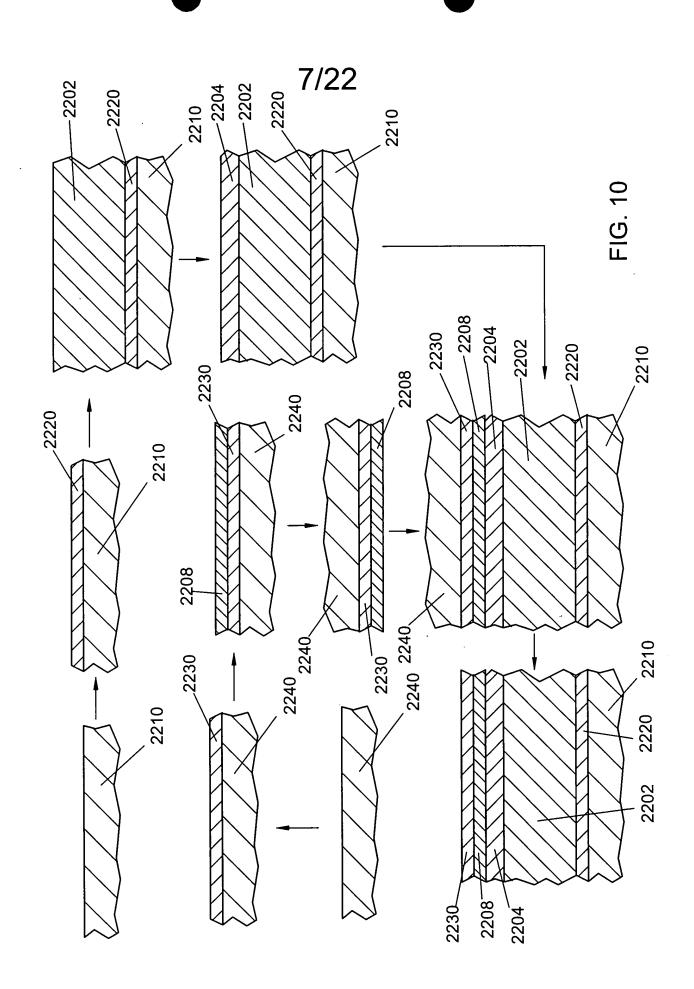
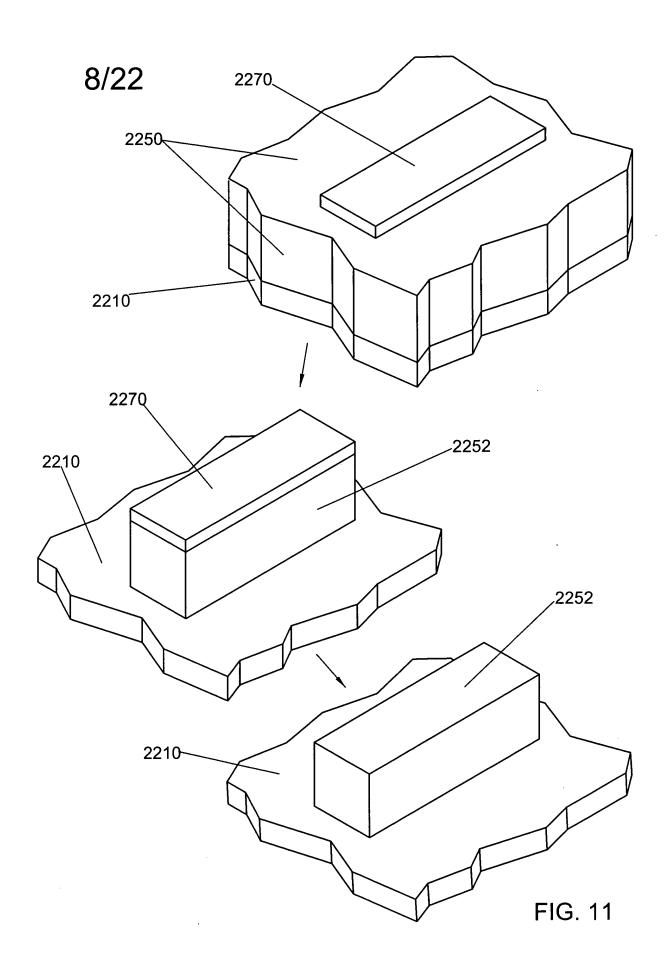
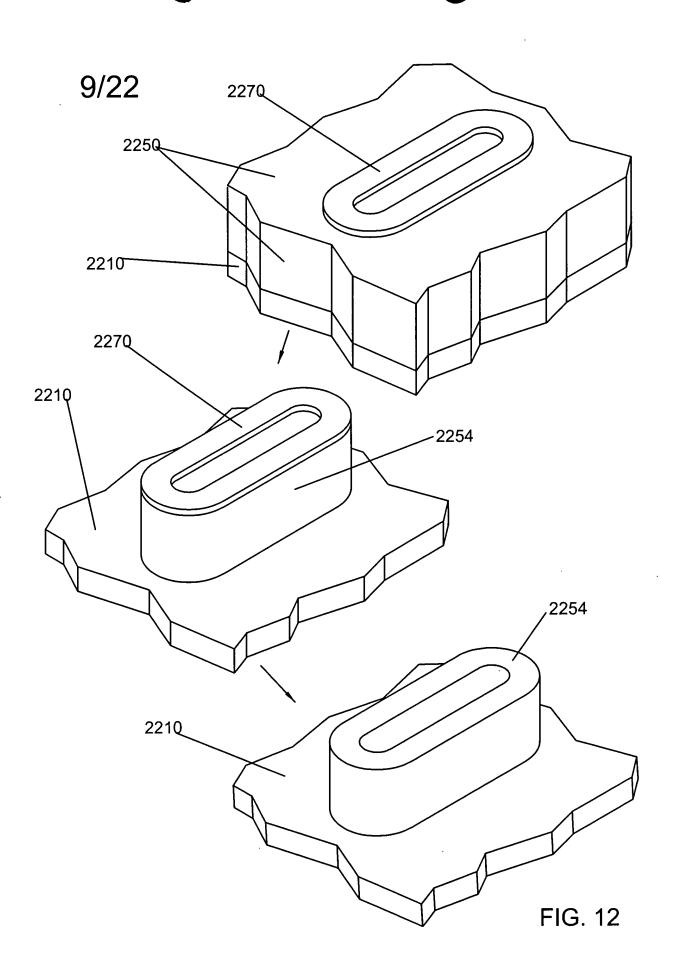
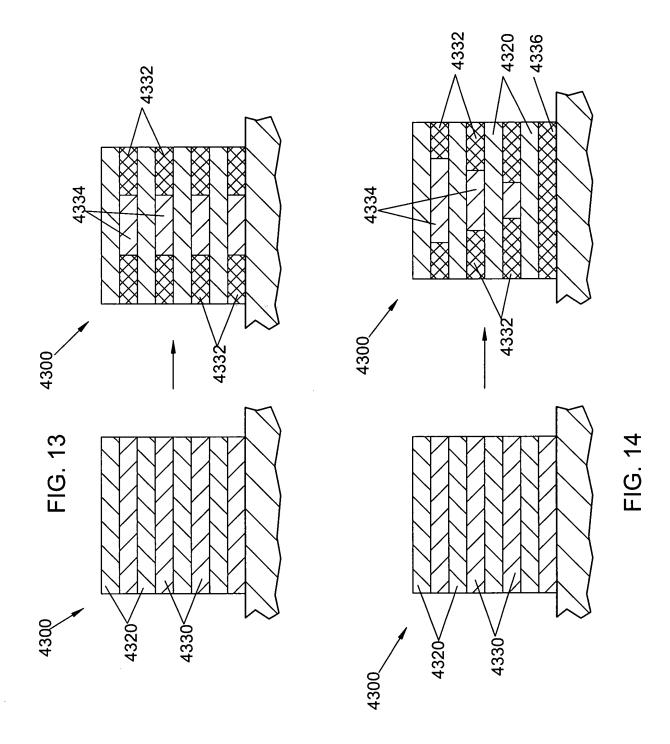


FIG. 9



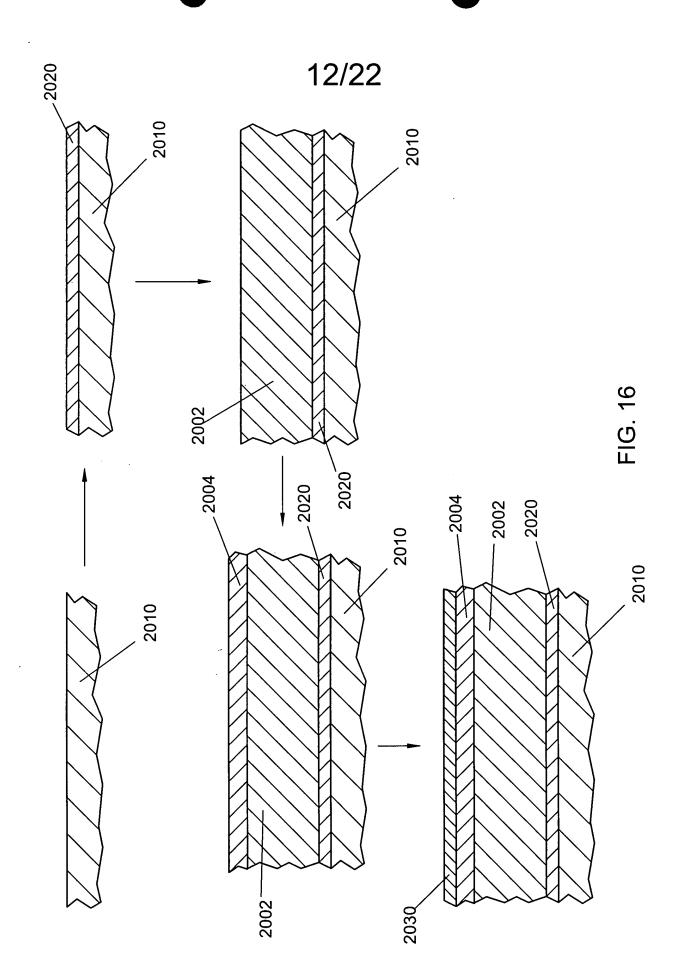


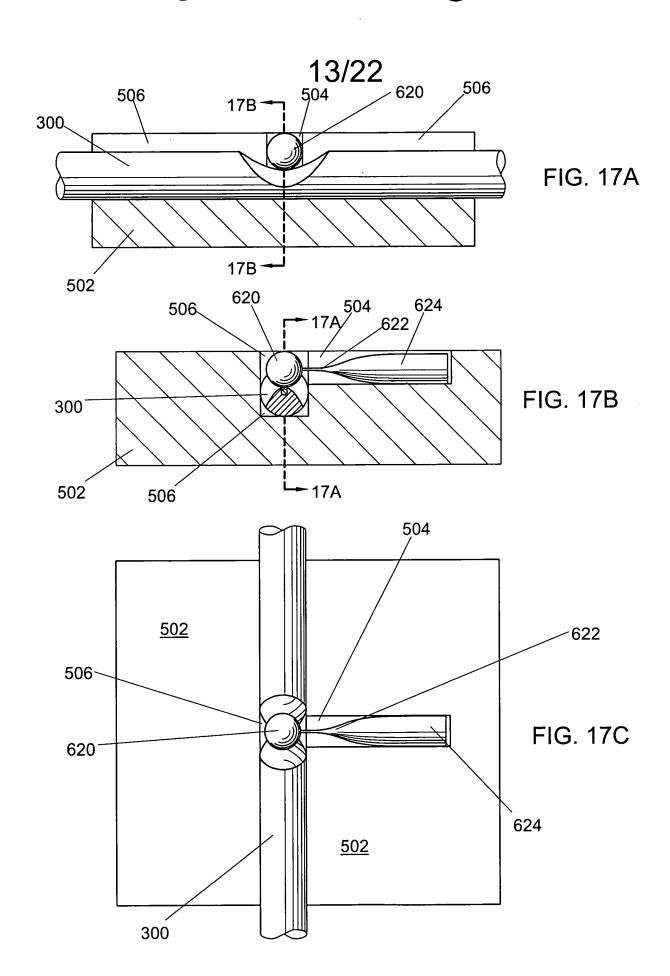


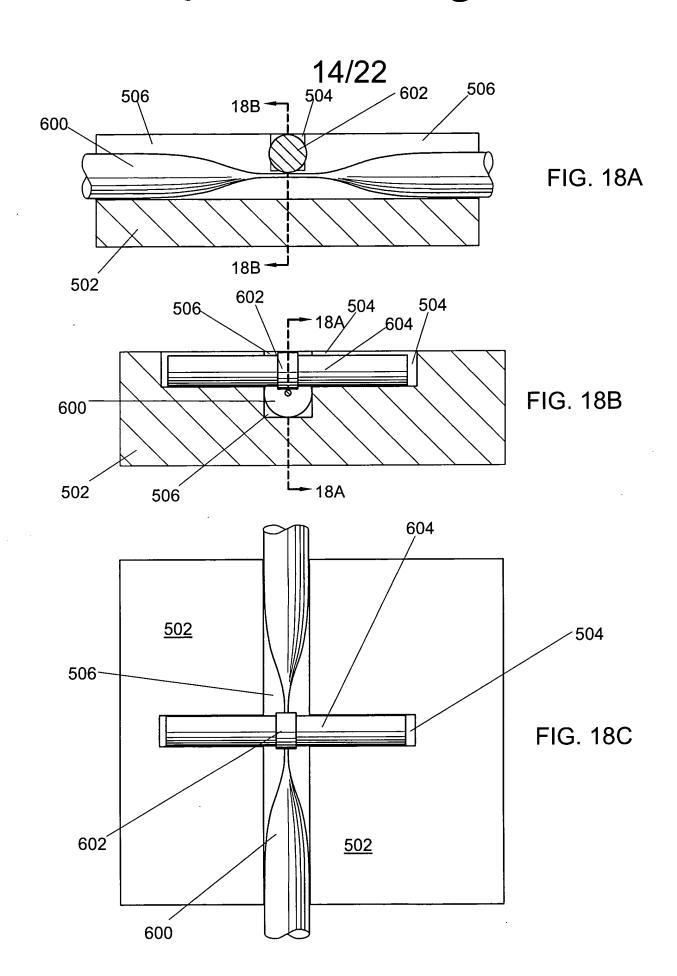


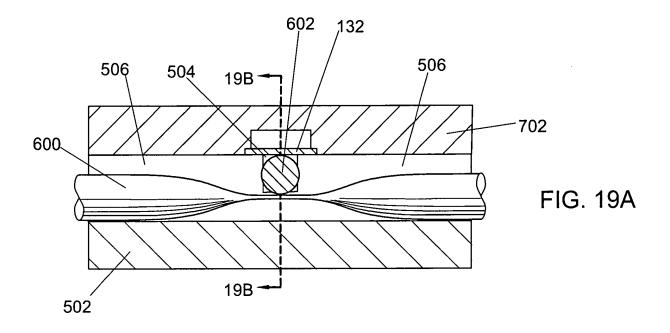
# 11/22 substrate 2010 1) deposit buffer/etch-stop layer (if desired) 2) deposit doped contact/etch-stop layer 2020 3) deposit buffer/etch-stop layer (if desired) deposit DBR stack 2002 (5-20 alternating low- and highindex quarter-wave layers, incorporating at least one EO layer, low index topmost layer) 1) deposit buffer/etch-stop layer (if desired) 2) deposit high-index core layer 2004 (between quarter- and half-wave thickness) 1) deposit buffer/etch-stop layer (if desired) 2) deposit doped contact/etch-stop layer 2030 3) deposit cladding/etch-stop layer (if desired)

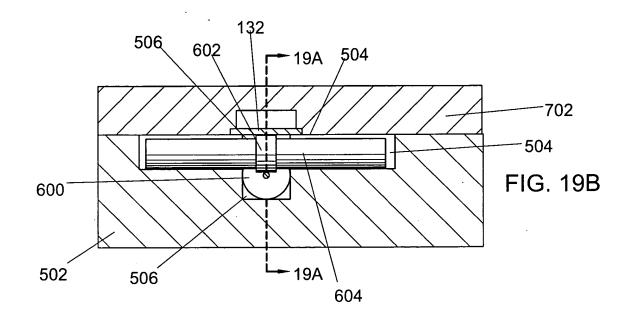
FIG. 15











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